

ICEM30D120W Silicon Carbide Schottky Diode

Product Summary			
I_F	$T_C=140^\circ\text{C}$	30A	Max
V_R		1200V	Min
T_j		175°C	Max
Q_C	V=800V	139nC	Typ

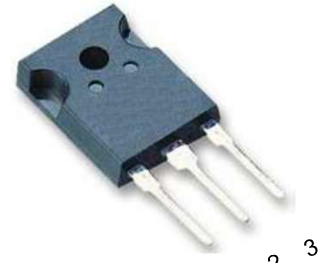
Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Positive Temperature Coefficient on V_F
- Temperature-Independent Switching Behaviour
- Extremely Fast Switching
- Optimized design for high performance power systems

Anode



Cathode



TO247
1:NC, 2:K,
3:A, 4:K
(TO-247)



Lead Free

Maximum ratings^a at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Continuous Forward Current	I_F	$T_C=25^\circ\text{C}$ $T_C=140^\circ\text{C}$	72 30	A
Non-Repetitive Forward Surge Current, $t_p=10\text{ms}$, Half Sine Wave Pulse	I_{FSM}	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	264 240	A
i^2t value $t_p=10\text{ms}$, Half Sine Wave Pulse	$\int j^2 dt$	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	348 288	A^2s
Operating Junction Temperature and Storage Temperature	T_j, T_{stg}		-55 to +175	$^\circ\text{C}$

^a Preliminary data sheet - Specifications subject to change.

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Thermal characteristics

Thermal resistance, junction-case	R_{thJC}		-	-	0.56	°C/W
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Electrical characteristics at $T_j=25^\circ\text{C}$, unless otherwise specified

Forward Voltage	V_F	$I_F=30\text{A}, T_j=25^\circ\text{C}$	-	1.42	1.7	V
		$I_F=30\text{A}, T_j=175^\circ\text{C}$	-	2.0	-	
Reverse Current	I_R	$V_R=1200\text{V}, T_j=25^\circ\text{C}$	-	1	10	μA
		$V_R=1200\text{V}, T_j=175^\circ\text{C}$	-	26	-	
Total Capacitive Charge	Q_C	$V=800\text{V}$	-	139	-	nC
Total Capacitance	C	$V_R=0\text{V}, f=100\text{ kHz}$	-	1937	-	pF
		$V_R=400\text{V}, f=100\text{ kHz}$		131		
		$V_R=800\text{V}, f=100\text{ kHz}$		97		

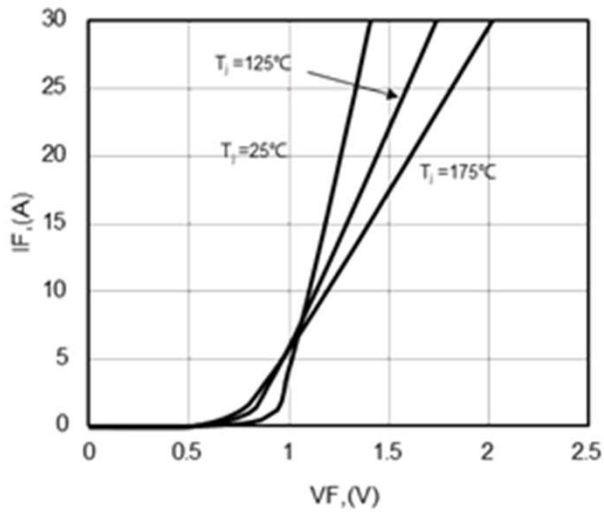


Fig1. Forward Characteristics

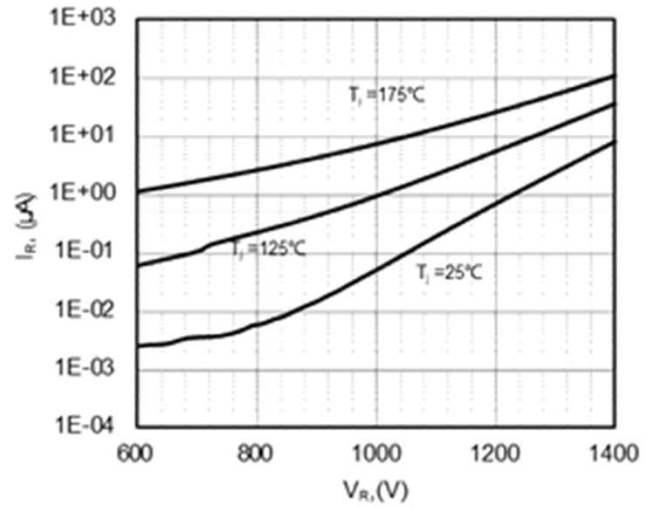


Fig2. Reverse Characteristics

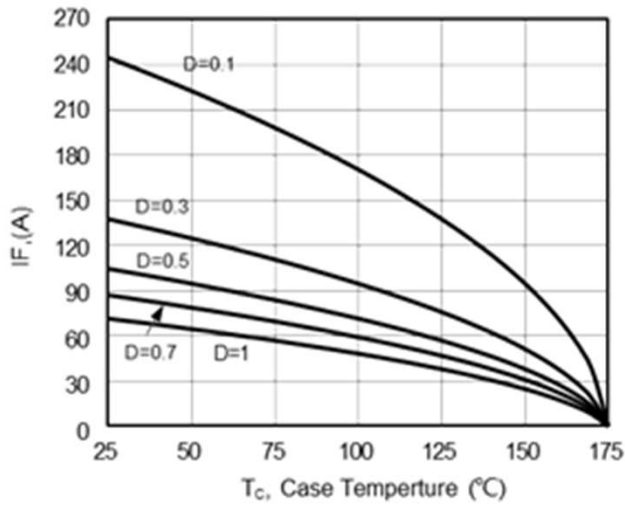


Fig3. Current Derating

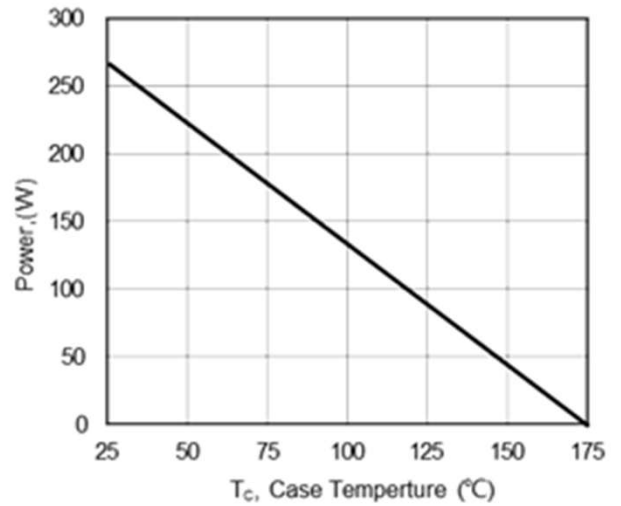


Fig4. Power Derating

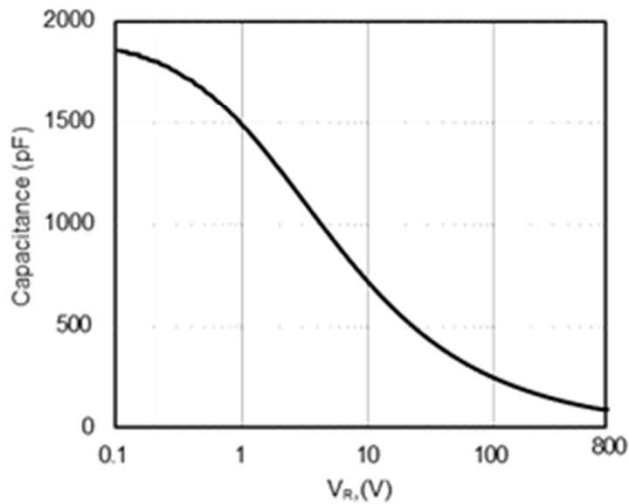


Fig5. Capacitance Characteristics

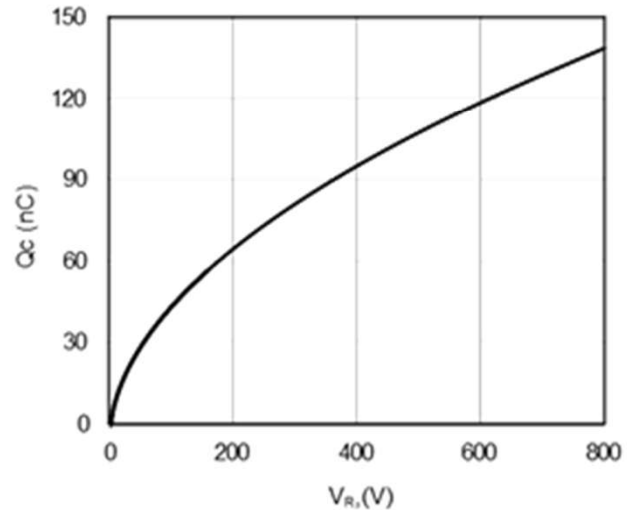


Fig6. Capacitance Charge

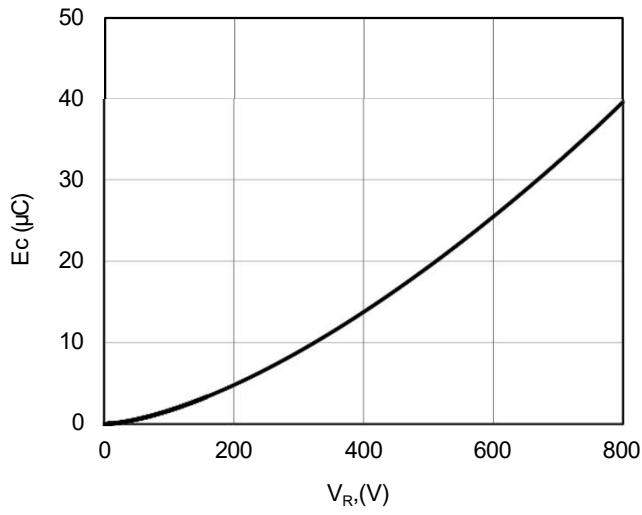


Fig7. Capacitance Stored Energy

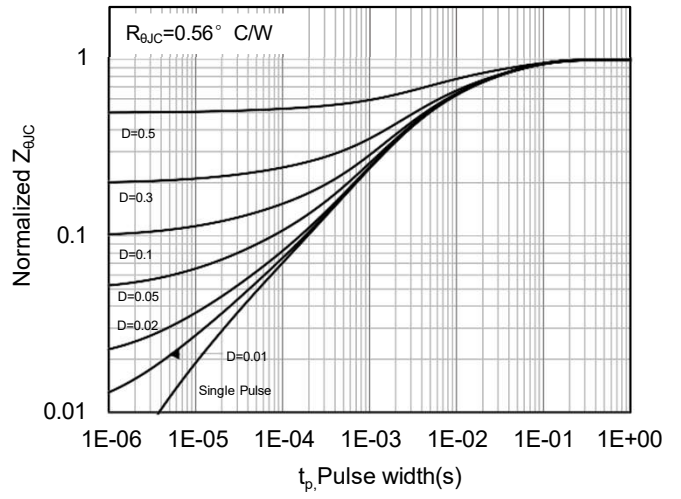


Fig8. Normalized Max. transient thermal impedance

Marking Information

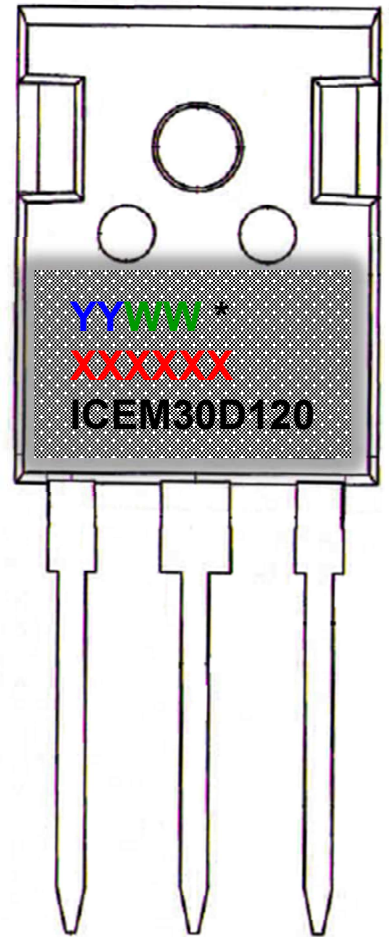
YY = Last two digits of the year

WW = Work week

***** = Site ID

XXXXXX = Lot ID

ICEM30D120 = ICE is Icemos logo and M30D120 is a designated device part number



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